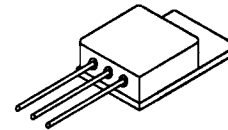




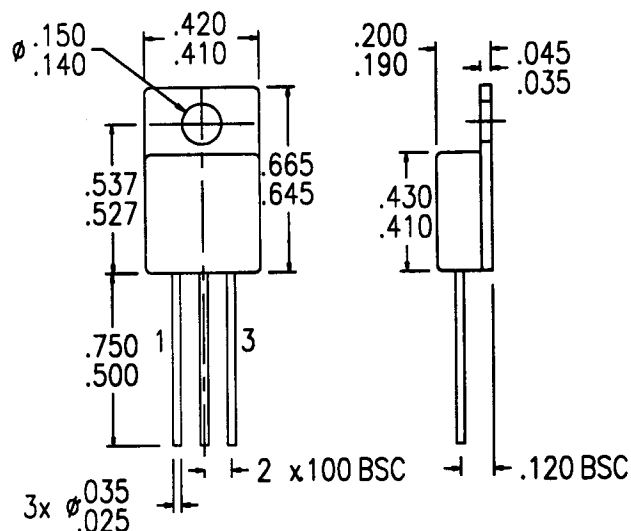
PRELIMINARY

SOLID STATE DEVICES, INC14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**SFF440J****Designer's Data Sheet****FEATURES:**

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed surface mount package
- Low inductance leads
- TX, TXV and Space Level screening available
- Replaces: IRF440 Types

**8 AMP
500 VOLTS
0.86Ω
N-CHANNEL
POWER MOSFET****TO-257****MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	500	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	6.9	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	2	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P _D	63 48	Watts

PACKAGE OUTLINE: TO-257**PIN OUT:****PIN 1: DRAIN
PIN 2: SOURCE
PIN 3: GATE****NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.****DATA SHEET #: F00087 A****MED**

SFF440J

PRELIMINARY

SSDI**SOLID STATE DEVICES, INC**14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**ELECTRICAL CHARACTERISTICS @ T_J=25 °C (Unless Otherwise Specified)**

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)		BV_{DSS}	500	---	---	V
Drain to Source on State Resistance (V _{GS} =10 V, I _D =60% Rated I _D)		R_{DS(on)}	---	0.72	0.86	Ω
On State Drain Current (V _{DS} >I _{D(on)} X R _{DS(on)} Max, V _{GS} =10 V)		I_{D(on)}	8	---	---	A
Gate Threshold Voltage (V _{DS} =V _{GS} , I _D =250μA)		V_{GS(th)}	2.0	---	4.0	V
Forward Transconductance (V _{DS} ≥50V, I _{DS} =60% rated I _D)		g_{fs}	4.9	7.4	---	S(Ω)
Zero Gate Voltage Drain Current (V _{DS} =max rated voltage, V _{GS} =0 V) (V _{DS} =80% rated V _{DS} , V _{GS} =0 V, T _A =125°C)		I_{DSS}	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V _{GS}	I_{GSS}	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	V _{GS} =10 Volts 80% rated V _{DS} I _D =8 A	Q_g Q_{gs} Q_{gd}	---	42 6 22	63 10 32	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	V _{DD} =50% rated V _{DS} I _D = 8 A R _G =9.1Ω R _D =30Ω	t_{d(on)} t_r t_{d(off)} t_f	---	14 23 50 20	21 35 74 30	nsec
Diode Forward Voltage (I _S =rated I _D , V _{GS} =0 V, T _J =25°C)		V_{SD}	---	---	2.0	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C I _F =rated I _D di/dt=100 A/μsec	t_{rr} Q_{RR}	210 2	460 4.2	970 8.9	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{GS} =0 Volts V _{DS} =25 Volts f= 1 MHz	C_{iss} C_{oss} C_{rss}	---	1300 180 45	---	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.